

**ELECTROPHORETIC DEPOSITION OF CdSe NANOPARTICLES
PHOTOANODE FOR QUANTUM DOTS SENSITIZED SOLAR CELLS**

by

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**Thesis submitted in fulfillment of the
requirements for the degree of
Doctor of Philosophy**

February 2019

ACKNOWLEDGEMENT

First of all, I would like to thank ALLAH for giving me time to finish my project. Then I would like to express my sincere gratitude to my main supervisor Assoc. Prof. Dr. Khatijah Aisha Yaacob and to my co-supervisor Prof. Dr. Ahmad Fauzi Bin Mohd. Noor for the continuous support of my Ph.D study with their deep technical knowledge, patience, and continual encouragement.

Furthermore, I would like to say my word of thanks to Universiti Sains Malaysia and School of Materials and Minerals Resources Engineering for providing the sufficient resources, facilities and instruments. In addition, I would like to thank the Dean of the School, Assoc. Prof. Ir. Dr. Syed Fuad Saiyid Hashim.

Besides, I would like to extend my sincere appreciation to all the technicians that had supported me directly or indirectly throughout my work especially; En. Azam, En. Azrul, Pn. Haslina, En. Zulkurnain, En. Rashid, En. Kemuridan, En. Mokhtar, En. Shahrul and to En Zharif from Science & Engineering Research Centre (SERC) for their assistance and cooperation provided in completing my project.

Last but not least, I would like to take this opportunity to convey my gratitude and appreciation to my friend Mustafa Ali Azhar, Haniah and Haymar for their support, helpful comments and suggestions. Not forgetting, my utmost gratitude to my family especially my sister, Lisdawati and my brother Nazril for their continuous support till end of my study and a special Duaa to my late mum and dad. I also would like to thank to Universiti Sains Malaysia RUI Grant No. 814185 and MyBrain15 for providing the financial support for my project.

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LIST OF ABBREVIATIONS

AC	Alternating Current
AFM	Atomic Force Microscopy
Ag ₂ S	Silver Sulfide
Au	Gold
Bi ₂ S ₃	Bismuth Sulfide
CBD	Chemical Bath Deposition
CB	Conduction Band
Cd(Ac) ₂	Cadmium Acetate
Cd(NO ₃) ₂	Cadmium Nitrate
CdS	Cadmium Sulfide
CdSe	Cadmium Selenide
CdSO ₄	Cadmium Sulfate
CdTe	Cadmium Telluride
CE	Counter Electrode
CIGS	Copper Indium Gallium Selenide
CNT	Carbon Nanotube
CoS	Cobalt Sulfide
CPE	Constant Phase Element
Cu ₂ S	Copper Sulfide
CuInS	Copper Indium Sulfide
DA	Direct Absorption
DCM	Dichloromethane
DSSC	Dye Sensitized Solar Cell
EDL	Electrical Double Layer

EPD	Electrophoretic Deposition
FF	Fill Factor
FTO	Fluorine Doped Tin Oxide
FTIR	Fourier Transform Infrared Spectroscopy
GuSCN	Guanidine Thiocyanat
H ₂ SO ₄	Sulphuric Acid
HCl	Hydrochloric Acid
HDA	Hexadecylamine
HNO ₃	Nitric Acid
HRTEM	High Resolution Transmission Electron Microscopy
HTM	Hole Transporting Material
ICP-OES	Inductively Coupled Plasma Optical Emission Spectroscopy
IPCE	Incident Photon to Current Conversion Efficiency
InAs	Indium Arsenide
InP	Indium Phosphide
J-V	Current Density-Voltage
K ₃ NTA	Potassium Nitrilotriacetate
KBr	Potassium Bromide
LED	Light Emitting Diode
Li ₂ S	Lithium Sulfide
MDA	Mercaptohexadecanoic
MEG	Multiple Exciton Generation
MPA	Mercaptopropionic Acid
MUA	Mercaptoundecanoic Acid
Na ₂ S	Sodium Sulfide
Na ₂ SO ₃	Sodium Sulfite
Na ₂ SeO ₃	Sodium Selenite